

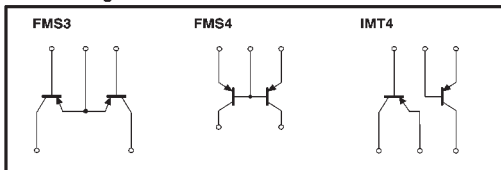
General purpose (dual transistors)

FMS3 / FMS4 / IMT4

●Features

- 1) Two 2SA1514K chips in an SMT package.
- 2) High breakdown voltage.

●Circuit diagrams



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	-120	V
Collector-emitter voltage	V_{CEO}	-120	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-50	mA
Power dissipation	P_C	300 (TOTAL)	mW *
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55~+150	°C

* 200mW per element must not be exceeded.

●Package, marking, and packaging specifications

Part No.	FMS3	FMS4	IMT4
Package	SMT5	SMT5	SMT6
Marking	S3	S4	T4
Code	T148	T148	T108
Basic ordering unit (pieces)	3000	3000	3000

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-120	—	—	V	$I_C = -50 \mu A$
Collector-emitter breakdown voltage	BV_{CEO}	-120	—	—	V	$I_C = -1 mA$
Emitter-base breakdown voltage	BV_{EBO}	-5	—	—	V	$I_E = -50 \mu A$
Collector cutoff current	I_{CO}	—	—	-0.5	μA	$V_{CB} = -100V$
Emitter cutoff current	I_{EO}	—	—	-0.5	μA	$V_{EB} = -4V$
DC current transfer ratio	h_{FE}	180	—	820	—	$V_{CE} = -6V, I_C = 2mA$
Transition frequency	f_T	—	140	—	MHz	$V_{CE} = -12V, I_E = 2mA, f = 100MHz$ *
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.5	V	$I_C/I_E = -10mA/-1mA$

* Transition frequency of the device.

(94S-389-A41)

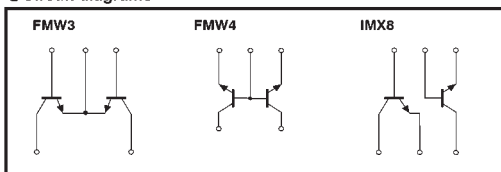
General purpose (dual transistors)

FMW3 / FMW4 / IMX8

●Features

- 1) Two 2SC3906K chips in an SMT package.
- 2) High breakdown voltage.

●Circuit diagrams



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	120	V
Collector-emitter voltage	V_{CEO}	120	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA
Power dissipation	P_C	300 (TOTAL)	mW *
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55~+150	°C

* 200mW per element must not be exceeded.

●Package, marking, and packaging specifications

Part No.	FMW3	FMW4	IMX8
Package	SMT5	SMT5	SMT6
Marking	S3	S4	T4
Code	T148	T148	T108
Basic ordering unit (pieces)	3000	3000	3000

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	120	—	—	V	$I_C = 50 \mu A$
Collector-emitter breakdown voltage	BV_{CEO}	120	—	—	V	$I_C = 1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E = 50 \mu A$
Collector cutoff current	I_{CO}	—	—	0.5	μA	$V_{CB} = 100V$
Emitter cutoff current	I_{EO}	—	—	0.5	μA	$V_{EB} = 4V$
DC current transfer ratio	h_{FE}	180	—	820	—	$V_{CE} = 6V, I_C = 2mA$
Transition frequency	f_T	—	140	—	MHz	$V_{CE} = -12V, I_E = 2mA, f = 100MHz$ *
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	$I_C/I_E = 10mA/1mA$

* Transition frequency of the device

(94S-398-C41)